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~~13~~¹³ (Once Amended) The method of claim 1, wherein the third material comprises a substrate material.

~~17~~¹⁷ (Once Amended) The method of claim 1, wherein the surface of the layer of the third material is biaxially textured.

~~18~~¹⁸ (Once Amended) The method of claim 1, wherein the third material comprises a single crystal material.

20. (Once Amended) A method of making a multi-layer article, comprising:
depositing a first material on a surface of a third material to form a deposited layer of the first material, the first material being selected from the group consisting of a buffer material and a superconductor material;

heating, at an oxygen gas pressure of less than about 700 Torr, a surface of the deposited layer of the first material to a temperature at least about 5°C above a temperature selected from the group consisting of a deposition temperature of the layer of the first material and a crystallization temperature of the layer of the first material to form a conditioned surface; and disposing a second material layer on the conditioned surface.

~~25~~²⁵ (Once Amended) The method of claim 20, wherein the third material comprises a substrate material.

~~26~~²⁶ (Once Amended) The method of claim 20, wherein the third material comprises a material selected from the group consisting of nickel and silver.

~~31~~³¹ (Once Amended) The method of claim 20, wherein the surface of the layer of the third material is biaxially textured.

~~32~~³² (Once Amended) The method of claim 20, wherein the third material comprises a single crystal material.

41. (Once Amended) A method of making a multi-layer article, comprising:
depositing a first material on a surface of a third material to form a deposited layer of the first material, the first material being selected from the group consisting of a buffer material and a superconductor material;
heating a surface of the deposited layer of the first material to a temperature at least about 5 °C above a temperature selected from the group consisting of a deposition temperature of the layer of the first material and a crystallization temperature of the layer of the first material to form a conditioned surface, the first material being disposed on a surface of a polycrystalline material; and
disposing a second material layer on the conditioned surface.

42. (Once Amended) The method of claim 55, wherein the environment further comprises hydrogen and an inert gas --